

## **Product Change Notification**



Product Group: Vishay Siliconix/May 20, 2014/PCN- SIL-0442014 Rev1

### **Fab Site Transfer**

**DESCRIPTION OF CHANGE:** For the 45M cell products listed in this notification we are changing the Fab site from Santa Clara, California, USA and Global Foundries, Singapore to Vishay Siliconix Itzehoe GmbH (VSIG) located at Fraunhoferstraße 1, 25524 Itzehoe, Germany. VSIG has been an automotive Fab with ISO14001 and TS16949 certifications for more than 10 years.

No changes have been made to the silicon process technology, wafer test, assembly process and final test. Production of the affected part from Santa Clara Fab and Global Foundries will be terminated per the time schedule in this notification and last time buy orders must be received within the specified timeframe.

**CLASSIFICATION OF CHANGE:** Fab Site Transfer

REASON FOR CHANGE: Closure of Santa Clara Fab and Global Foundries

EXPECTED INFLUENCE ON QUALITY/RELIABILTY/PERFORMANCE: None

**PRODUCT CATAGORY:** Automotive MOSFETs

VISHAY PART NUMBERS AFFECTED: Affected part numbers are listed on the following page

VISHAY BRAND(s): Vishay-Siliconix

**TIME SCHEDULE:** Last time buy orders are required by 01-Oct-2014 for Global Foundries and 31-Dec-2014 for Santa Clara Fab. Last shipments should be scheduled before 30-June-2015.

**QUALIFICATION DATA:** All products listed in this notification are manufactured using 45M cell process technology which is AEC Q101 qualified. Please refer to subsequent pages to see summary of qualification report for the lead 45M cell product from VSIG Fab. Qualification report for individual part type will be provided in PPAP and upon request.

**SAMPLE AVAILABILITY:** Schedule of availability of qualified samples from VSIG Fab is listed on the following page. For samples, please email <a href="mailto:automos.pcn@Vishay.com">automos.pcn@Vishay.com</a> with subject PCN-SIL-0442014 and include date by which samples are needed, required quantity and ship-to address.

ISSUED BY: Shishir Rai, Product Marketing Manager (E-mail: Shishir.Rai@Vishay.com)

For further information, please contact your regional Vishay office.

The Americas

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Vishay Intertechnology, Inc.



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#### **VISHAY PART NUMBERS AFFECTED:**

Affected Vishay Part Number	Qualified Sample Availability from VSIG Fab
SQM110N05-06L-GE3	Available
SQJ850EP-T1-GE3	Available
SQJ850EP-T2-GE3	Available
SQJ840EP-T1-GE3	Available
SQD40N10-25-GE3	Available
SQD40N10-25-T4-GE3	Available
SQD30N05-20L-GE3	Available
SQD25N06-22L-GE3	Available
SQD25N06-22L-T4GE3	Available
SQR40N10-25-GE3	Jun-14
SQJ968EP-T1-GE3	Jun-14
SQJ960EP-T1-GE3	Jun-14
SQJ844AEP-T1-GE3	Jun-14
SQD40N06-14L-GE3	Jun-14
SQ9945BEY-T1-GE3	Jun-14
SQ4946AEY-T1-GE3	Jun-14
SQ4850EY-T1-GE3	Jun-14
SQ4840EY-T1-GE3	Jun-14
SQ4410EY-T1-GE3	Jun-14

#### **QUALIFICATION REPORT:**

Qualification report for lead product SQM100N10-10-GE3 manufactured using 45M cell process technology at VSIG Fab is provided in subsequent pages. Qualification report for the individual parts listed above will be provided in PPAP and upon request.



## **Production Part Approval - Environmental Test Summary**

Supplier:Vishay SiliconixGeneral Specification:AEC-Q101Supplier Part Number:SQM100N10-10-GE3Assembly Site:Kaohsiung, Taiwan ROCProcess Technology:45M Cell N-Channel G2Fab Site:VSIG, Itzehoe Germany

			# OT				
tem	Test	Test Conditions	Lots	S.S.	# Failed	<b>Additional Requirements</b>	Remarks
1	Pre- and Post Stress Electrical Test		*	All	0		
	Pre-conditioning: Performed on surface mount devices						
	(SMDs) prior to Temp Cycle, Autoclave, HAST, Power Cycle						
2	stresses only	J-STD-020C	*	All	0	@260 C	
_	External Visual: Inspect device construction, marking and	Electricale and descripe	*				
3	workmanship. Electrical test not required.	Electricals per drawing	-	All	0		Evaluation
4	Parametric Verification		3	30	0		1.
							2.
							3
	High Temperature Reverse Bias (HTRB):						
	1000 hours max rated junction temperature specified in the						
5	user/supplier specification with device reverse biased to 80%	175C 1000 HRS	3	77	0	DEVICE SPECIFIC:	Evaluation
Ū	of maximum breakdown voltage specified or max junction					221.02 0. 20 10.	1. 1380271
	temperature to avoid thermal runaway. TEST before, at 500						2. 1380272
	hours, and 1000 hours. JESD22 A108						3. 1380273
	UI T C C C D: (UTOD)						3. 1300273
	High Temperature Gate Bias (HTGB):						
	1000 hours at Ta = device maximum rated junction						
6	temperature with gate biased at 100% of maximum gate	175C 1000 HRS	3	77	0	DEVICE SPECIFIC:	Evaluation
	voltage rating indicated in the detail specification with device						1. 1380271
	OFF. TEST before, at 500 hours, and 1000 hours. JESD22						2. 1380272
	A108						3. 1380273
	Temperature Cycling: JESD22 A-104, Air to air. (See						Evaluation
7	Reliability Product Data Summary):	1000CYC -65C ~ 150C	3	77	0	DEVICE SPECIFIC:	1. 1380271
'	Reliability Froduct Data Summary).	1000010-030 ~ 1300	3	''	0	DEVICE SEEDING.	2. 1380272
							3. 1380273
							Evaluation
8	Autoclave (Pressure Pot)	Ta = 121C, RH = 100%, 15psig, 96	3	77	0	DEVICE SPECIFIC:	1. 1380271
0	Autoclave (Pressure Pot)	hrs: Test before and after AC.	3	11	U	DEVICE SPECIFIC.	2. 1380272
							3. 1380273
							Evaluation
0 -14	LIACT	4000 050/ DIL 400 LIDO				DEVICE OPEQUEIO	1. 1380271
9 alt	HASI	130C, 85% RH, 100 HRS	3	77	0	DEVICE SPECIFIC:	2. 1380272
							3. 1380273
							Evaluation
	Intermittent Operational Life (Power Cycle)						1. 1380271
10	Delta Tj = 100C	8572 CYC	3	77	0	DEVICE SPECIFIC:	2. 1380272
	20.00.						
							3. 1380273



## **Production Part Approval - Environmental Test Summary**

Supplier:Vishay SiliconixGeneral Specification:AEC-Q101Supplier Part Number:SQM100N10-10-GE3Assembly Site:Kaohsiung, Taiwan ROCProcess Technology:45M Cell N-Channel G2Fab Site:VSIG, Itzehoe Germany

			# OT				_
tem	Test	Test Conditions	Lots	S.S.	# Failed	Additional Requirements	Remarks
	ESD Characterization - NOTE: Unless protected by internal ESD-specific protection circuitry, MOSFETs only have intrinsic protection that is dependent on the size of die and other						Evaluation 1.1340081
11		Human Model	1	10	0	Passed5.40KV AEC Q101	
	the professional professional professional professional	Machine Model	1	10	0	Passed 1.10KV AEC Q101	
12	Destructive Physical Analysis	Cross-section / Cratering, CDF-AEC-Q101-004 Section 4	1	2x2	0		Evaluation 1.1340081
	Physical Dimensions: Verify physical dimensions to the applicable user device packaging specification for dimensions	Siliconix Print Dimensions	N/A	N/A	N/A		See PPAP
14	Termianl Strength	Ollicoriix i Tirk Diriterisions	N/A	N/A	N/A		SMD Device
	Resistance to Solvent		N/A	N/A	N/A		Laser Marked
	Constant Acceleration		N/A	N/A	N/A		SMD Device
	Vibration Variable Frequency		N/A	N/A	N/A		SMD Device
	Mechanical Shock		N/A	N/A	N/A		SMD Device
	Hermiticity		N/A	N/A	N/A		SMD Device
20	Resistance to Solder Heat (Solder Dunk)	JESD22 B-106-A, 260C, 10sec. Test before and after RSH. SMD devices shall be fully submerged during test	3	55		GENERIC	Evaluation 1. 2. 3.
21	Solderability	Pb-Free - JESD201	3	15	0	GENERIC	Evaluation 1. 2. 3.
22	Thermal Resistance	JESD24-3	1	10	0	DEVICE SPECIFIC:	Evaluation 1. 1340479 2.
23	Wire Bond Strength	MIL-STD-750 Method 2037	3	40	0	GENERIC	Evaluation 1. 2.



## **Production Part Approval - Environmental Test Summary**

ltom	T	Took Conditions	# OT		# Failed	Additional Demoinements	Domonto
	olier: olier Part Number: ess Technology:	Vishay Siliconix SQM100N10-10-GE3 45M Cell N-Channel G2		General Specification: Assembly Site: Fab Site:		Assembly Site:	AEC-Q101 Kaohsiung, Taiwan ROC VSIG, Itzehoe Germany

l4 a	Tool	Toot Conditions	# OT		# Faila d	Additional Descripements	Domonico
Item	Test	Test Conditions	Lots	S.S.	# Falled	Additional Requirements	Remarks
							Evaluation
24	Bond Shear	AEC-Q101-003	3	40	0	GENERIC	1.
							2.
							Evaluation
							Evaluation
25	Die Shear	MIL-STD-750 Method 2017				GENERIC	1.
			3	10	0		3
26	UIS Testing	Non-destructive mode	100%	100%	0		100% tested at Final Test
	0.0		. 50 /0	. 5070			10070 toolog at 1 mai 1 oot
27	Dielectric Integrity	Non-destructive mode	100%	100%	0		100% tested at Final Test

Note: \* = Samples taken from many lots

Prepared by	: Julan Chen	
Reliability É		5/16/2014

Approved by: Arthur Chiang	
Director of Reliability	5/16/2014
Director of Reliability	3/10/2017